

Improved Flash Memory Cell Process using a Hardmask

ABSTRACT OF THE INVENTION

A method is described for forming a memory structure using
5 a hardmask (65). The hardmask (65) protects the second
polysilicon layer (55) during a SAS etch process. In addition,
sidewall structures (95) are formed which protect the inter-
polysilicon dielectric layer (45) during the hardmask (65) etch
process.

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